

Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

I_{F(AV)} **1660 A**
V_{RRM} **200~600 V**
I_{FSM} **17 kA**
I²t **1445 10³A²s**

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Double side cooled,	190			1660	A
						1410	
V _{RRM}	Repetitive peak reverse voltage	V _{RRM} tp=10ms V _{RSM} =V _{RRM} +100V	190	200		600	V
I _{RRM}	Repetitive peak current	V _{RM} =V _{RRM}	190			30	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	190			17	kA
I ² t	I ² T for fusing coordination					1445	A ² s*10 ³
V _{FO}	Threshold voltage		190			0.78	V
r _F	Forward slop resistance					0.25	mΩ
V _{FM}	Peak on-state voltage	I _{FM} =1200A, F=7.0kN	190			1.10	V
Q _{rr}	Recovery charge	I _{FM} =1000A, tp=1000μs, di/dt=-20A/μs, V _R =50V	190		1600		μC
R _{th(j-C)}	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 7.0kN				0.045	°C /W
R _{th(C-h)}	Thermal resistance case to heat sink					0.010	
F _m	Mounting force			5.3		10	kN
T _{stg}	Stored temperature			-40		190	°C
W _t	Weight				80		g
Outline		ZT25aT					

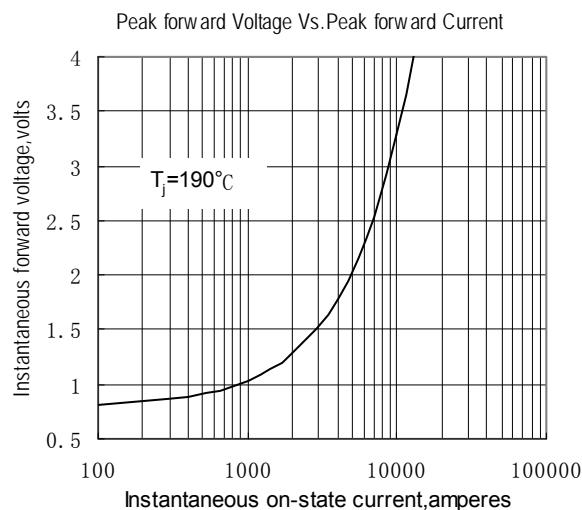


Fig.1

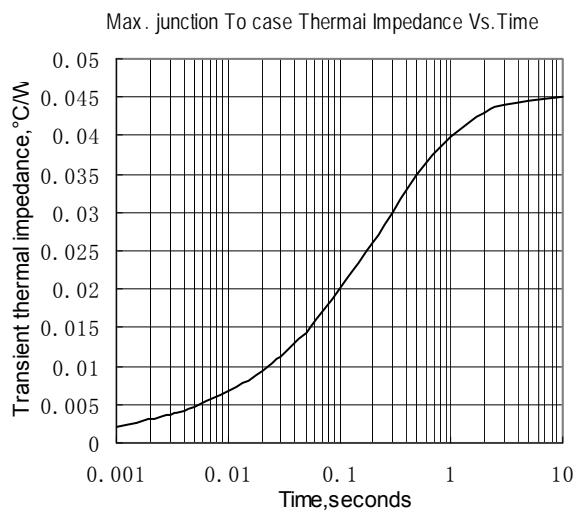


Fig.2

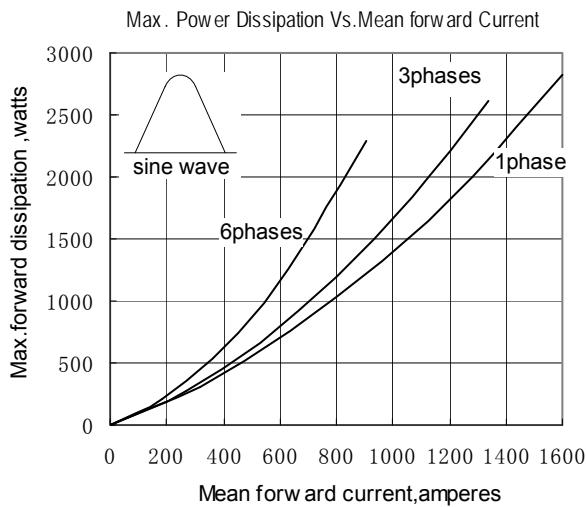


Fig.3

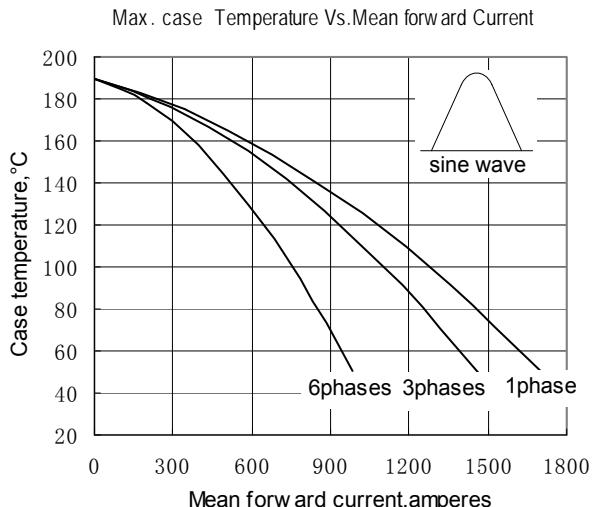


Fig.4

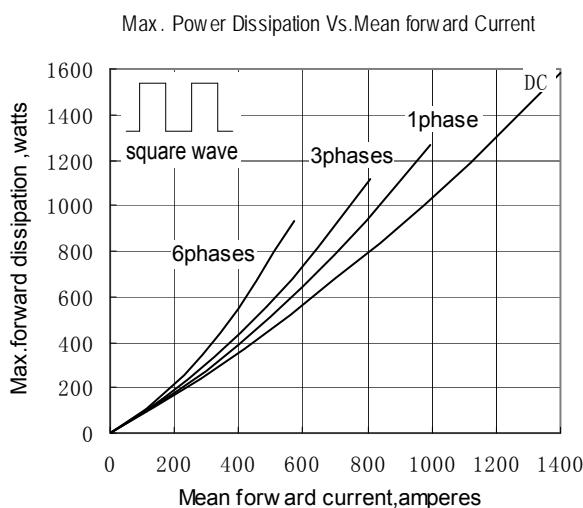


Fig.5

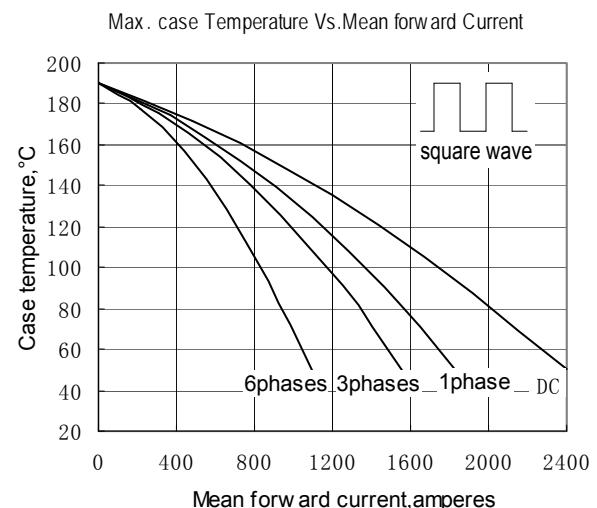


Fig.6

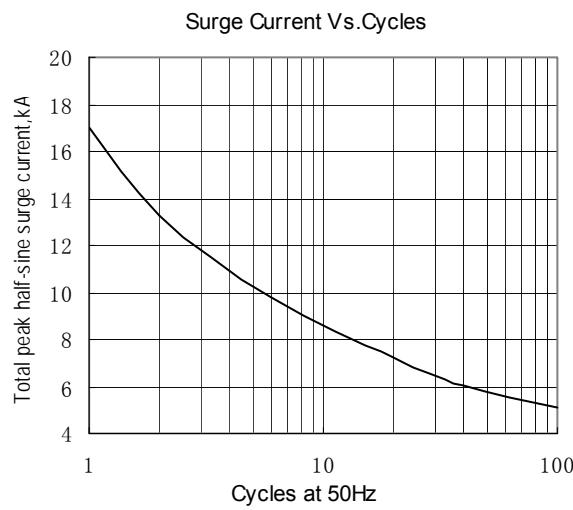


Fig.7

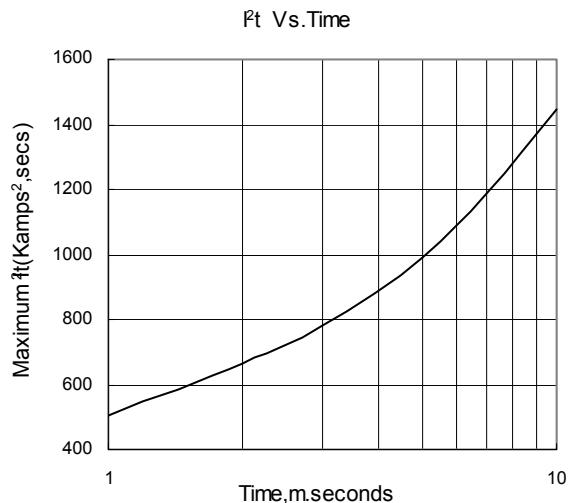


Fig.8

Outline: